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FDB0190N807L N-Channel PowerTrench[®] MOSFET 80 V, 270 A, 1.7 m Ω

Features

- Max r_{DS(on)} = 1.7 mΩ at V_{GS} = 10 V, I_D = 34 A
- Max $r_{DS(on)}$ = 2 m Ω at V_{GS} = 8 V, I_D = 31 A
- Fast Switching Speed
- Low Gate Charge
- \blacksquare High Performance Trench Technology for Extremely Low $R_{DS(on)}$
- High Power and Current Handling Capability
- RoHS Compliant

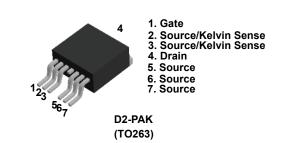


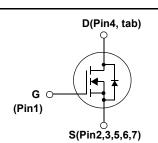
General Description

This N-Channel MOSFET is produced using Fairchild Semiconductor's advance PowerTrench[®] process that has been especially tailored to minimize the on-state resistance while maintaining superior ruggedness and switching performance for industrial applications.

Applications

- Industrial Motor Drive
- Industrial Power Supply
- Industrial Automation
- Battery Operated tools
- Battery Protection
- Solar Inverters
- UPS and Energy Inverters
- Energy Storage
- Load Switch





MOSFET Maximum Ratings T_C = 25 °C unless otherwise noted.

| Symbol | Parameter | | | Ratings | Units | |
|-----------------------------------|--|------------------------|----------|-------------|-------|--|
| V _{DS} | Drain to Source Voltage | | | 80 | V | |
| V _{GS} | Gate to Source Voltage | | | ±20 | V | |
| I _D | Drain Current -Continuous | T _C = 25°C | (Note 5) | 270 | A | |
| | -Continuous | T _C = 100°C | (Note 5) | 190 | | |
| | -Pulsed | | (Note 4) | 1440 | | |
| E _{AS} | Single Pulse Avalanche Energy | | (Note 3) | 777 | mJ | |
| P _D | Power Dissipation | T _C = 25°C | | 250 | w | |
| | Power Dissipation $T_A = 25^{\circ}C$ (Note 1a) | | | 3.8 | VV | |
| T _J , T _{STG} | Operating and Storage Junction Temperature Range | | | -55 to +175 | °C | |

| $R_{	ext{	heta}JC}$ | Thermal Resistance, Junction to Case | (Note 1) | 0.6 | °C/W |
|---------------------|---|-----------|-----|------|
| $R_{	ext{	heta}JA}$ | Thermal Resistance, Junction to Ambient | (Note 1a) | 40 | C/W |

Package Marking and Ordering Information

| Device Marking | Device | Package | Reel Size | Tape Width | Quantity |
|----------------|--------------|-----------|-----------|------------|-----------|
| FDB0190N807L | FDB0190N807L | D2-PAK-7L | 330 mm | 24 mm | 800 units |

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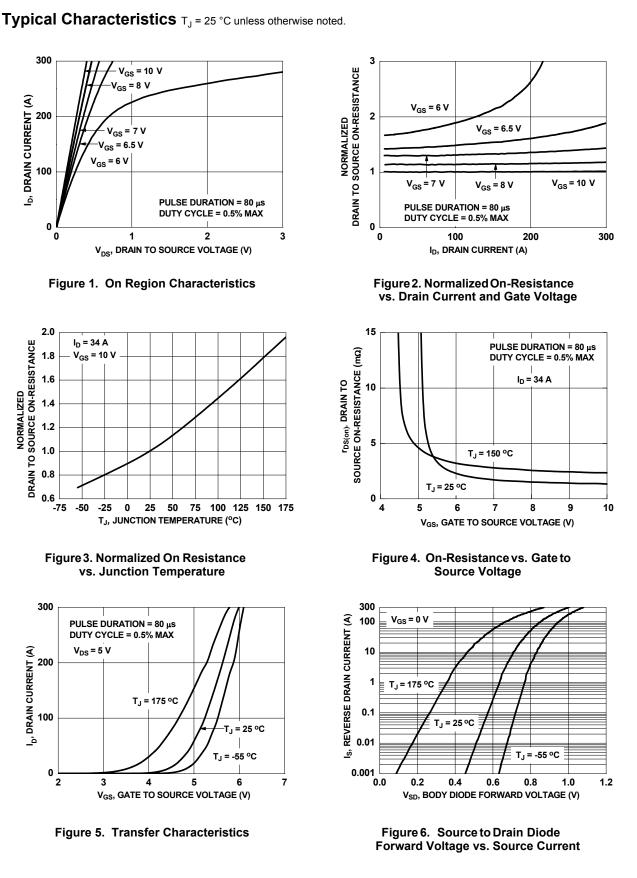
| Symbol | Parameter | Test Conditions | Min. | Тур. | Max. | Units |
|--|--|--|------|-----------------------|--------------------------|--------------------------|
| Off Chara | acteristics | | | | | |
| BV _{DSS} | Drain to Source Breakdown Voltage | I _D = 250 μA, V _{GS} = 0 V | 80 | | | V |
| $\frac{\Delta BV_{DSS}}{\Delta T_{J}}$ | Breakdown Voltage Temperature Coefficient | $I_D = 250 \ \mu\text{A}$, referenced to 25 °C | | 34 | | mV/°C |
| IDSS | Zero Gate Voltage Drain Current | V _{DS} = 64 V, V _{GS} = 0 V | | | 1 | μA |
| I _{GSS} | Gate to Source Leakage Current | $V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$ | | | ±100 | nA |
| | acteristics | | | 1 | I | 1 |
| V _{GS(th)} | Gate to Source Threshold Voltage | V _{GS} = V _{DS} , I _D = 250 μA | 2 | 2.9 | 4 | V |
| $\frac{\Delta V_{GS(th)}}{\Delta T_{J}}$ | Gate to Source Threshold Voltage Temperature Coefficient | $I_D = 250 \ \mu$ A, referenced to 25 °C | | -13 | | mV/°C |
| | Static Drain to Source On Resistance | V _{GS} = 10 V, I _D = 34 A | | 1.3 | 1.7 | |
| r _{DS(on)} | | V _{GS} = 8 V, I _D = 31 A | | 1.5 | 2 | mΩ |
| | | V_{GS} = 10 V, I _D = 34 A, T _J = 150°C | | 2.3 | 4.3 | |
| 9 _{FS} | Forward Transconductance | V _{DS} = 10 V, I _D = 34 A | | 133 | | S |
| | Output Capacitance Reverse Transfer Capacitance | ─ V _{DS} = 40 V, V _{GS} = 0 V, f = 1 MHz | | 1990 235 | 2790 330 | pF pF |
| C _{rss} | | f = 1 MHz | | | | • |
| R _g | Gate Resistance | | | 2.9 | | Ω |
| o | g Characteristics | | | | | |
| Switching | The Or Deley Terry | | | 60 | 96 | ns |
| | Turn-On Delay Time | V _{DD} = 40 V, I _D = 34 A, | | 78 | 125 | ns |
| t _{d(on)} | Rise Time | V _{DD} = 40 V, I _D = 34 A, | | | | ns |
| t _{d(on)} | | $V_{\text{DD}} = 40 \text{ V}, \text{ I}_{\text{D}} = 34 \text{ A}, \\ V_{\text{GS}} = 10 \text{ V}, \text{ R}_{\text{GEN}} = 6 \Omega$ | | 98 | 157 | |
| t _{d(on)} t _r t _{d(off)} t _f | Rise Time | | | 98 50 | 157 80 | ns |
| $t_{d(on)}$ t_r $t_{d(off)}$ t_f Q_g | Rise Time Turn-Off Delay Time Fall Time Total Gate Charge | V _{GS} = 10 V, R _{GEN} = 6 Ω | | 50 178 | | nC |
| t _{d(on)} t _r t _{d(off)} t _f Q _g Q _{gs} | Rise Time Turn-Off Delay Time Fall Time Total Gate Charge Gate to Source Gate Charge | | | 50 178 60 | 80 | nC nC |
| t _{d(on)} t _r t _{d(off)} t _f Q _g | Rise Time Turn-Off Delay Time Fall Time Total Gate Charge | V_{GS} = 10 V, R_{GEN} = 6 Ω - V _{DD} = 40 V, I _D = 34 A, | | 50 178 | 80 | nC |
| t _{d(on)} t _r t _{d(off)} t _f Q _g Q _{gs} Q _{gd} | Rise Time Turn-Off Delay Time Fall Time Total Gate Charge Gate to Source Gate Charge | V_{GS} = 10 V, R_{GEN} = 6 Ω - V _{DD} = 40 V, I _D = 34 A, | | 50 178 60 | 80 | nC nC |
| t _{d(on)} t _r t _{d(off)} t _f Q _g Q _{gs} Q _{gd} | Rise Time Turn-Off Delay Time Fall Time Total Gate Charge Gate to Source Gate Charge Gate to Drain "Miller" Charge | $V_{GS} = 10 \text{ V}, \text{ R}_{GEN} = 6 \Omega$ - V _{DD} = 40 V, I _D = 34 A, - V _{GS} = 10 V | | 50 178 60 | 80 | nC nC |
| t _{d(on)} t _r t _{d(off)} t _f Q _g Q _{gs} Q _{gd} Drain-So | Rise Time Turn-Off Delay Time Fall Time Total Gate Charge Gate to Source Gate Charge Gate to Drain "Miller" Charge urce Diode Characteristics | $V_{GS} = 10 \text{ V}, \text{ R}_{GEN} = 6 \Omega$ - V _{DD} = 40 V, I _D = 34 A, - V _{GS} = 10 V de Forward Current | | 50 178 60 | 80 249 | nC nC nC |
| t _{d(on)} t _r t _{d(off)} t _f Q _g Q _{gg} Q _{gd} Drain-So I _S I _S | Rise Time Turn-Off Delay Time Fall Time Total Gate Charge Gate to Source Gate Charge Gate to Drain "Miller" Charge urce Diode Characteristics Maximum Continuous Drain to Source Diode | $V_{GS} = 10 \text{ V}, \text{ R}_{GEN} = 6 \Omega$ - V _{DD} = 40 V, I _D = 34 A, - V _{GS} = 10 V de Forward Current | | 50 178 60 | 80 249 270 | nC nC nC |
| t _{d(on)} t _r t _{d(off)} t _f Q _g Q _{gg} Q _{gd} Drain-Sol | Rise Time Turn-Off Delay Time Fall Time Total Gate Charge Gate to Source Gate Charge Gate to Drain "Miller" Charge urce Diode Characteristics Maximum Continuous Drain to Source Diode Feature | $V_{GS} = 10 \text{ V}, \text{ R}_{GEN} = 6 \Omega$ $V_{DD} = 40 \text{ V}, \text{ I}_{D} = 34 \text{ A},$ $V_{GS} = 10 \text{ V}$ de Forward Current orward Current | | 50 178 60 32 | 80 249 270 1440 | nC nC nC A A |

2. Pulse Test: Pulse Width < 300 μ s, Duty cycle < 2.0 %.

3. E_{AS} of 777 mJ is based on starting T_J = 25 °C, L = 0.3 mH, I_{AS} = 72 A, V_{DD} = 72 V, V_{GS} = 10 V. 100% test at L = 0.1 mH, I_{AS} = 104 A.

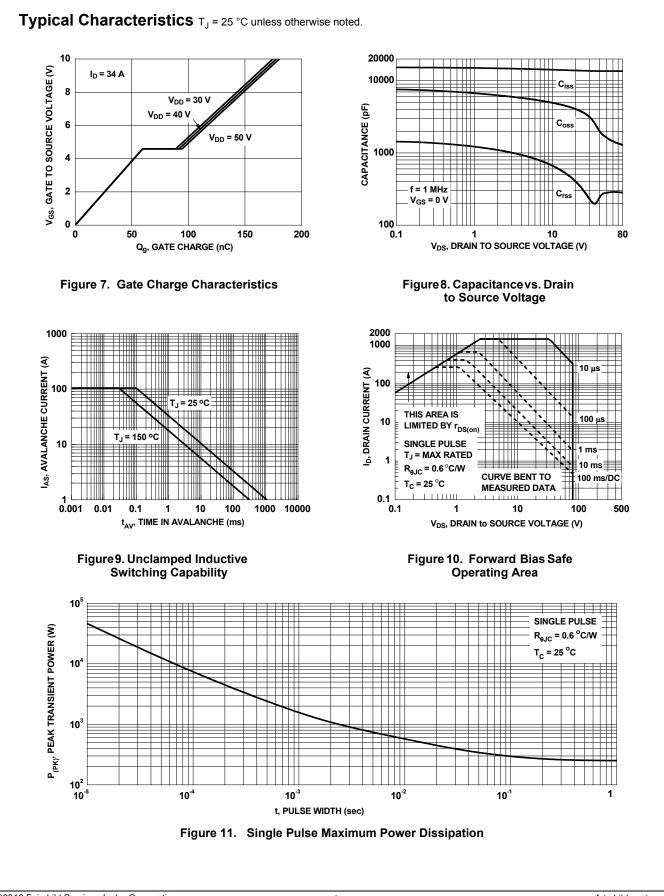
4. Pulsed Id please refer to Figure "Forward Bias Safe Operating Area" for more details.

5. Computed continuous current limited to Max Junction Temperature only, actual continuous current will be limited by thermal & electro-mechanical application board design.

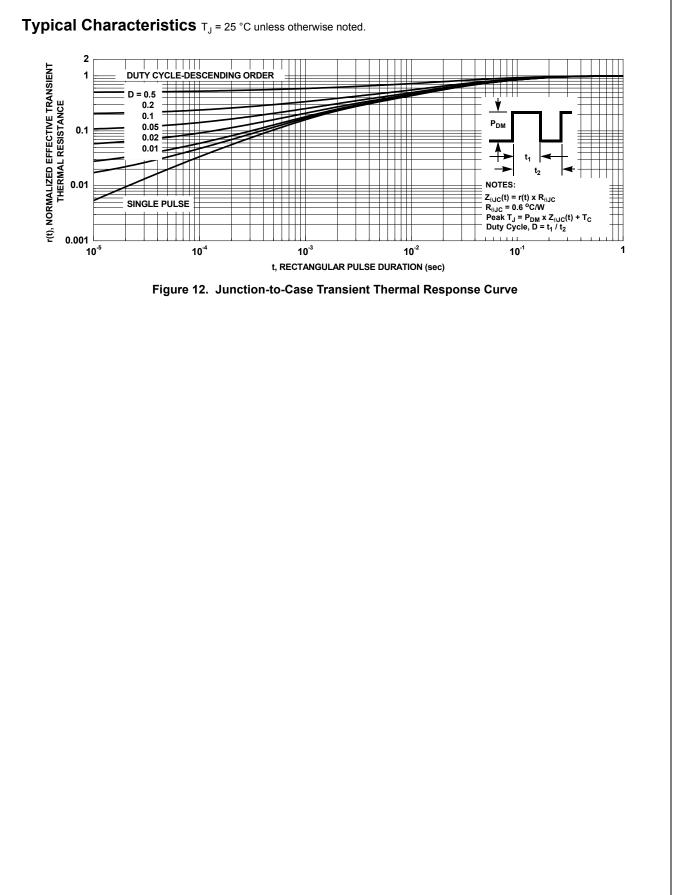


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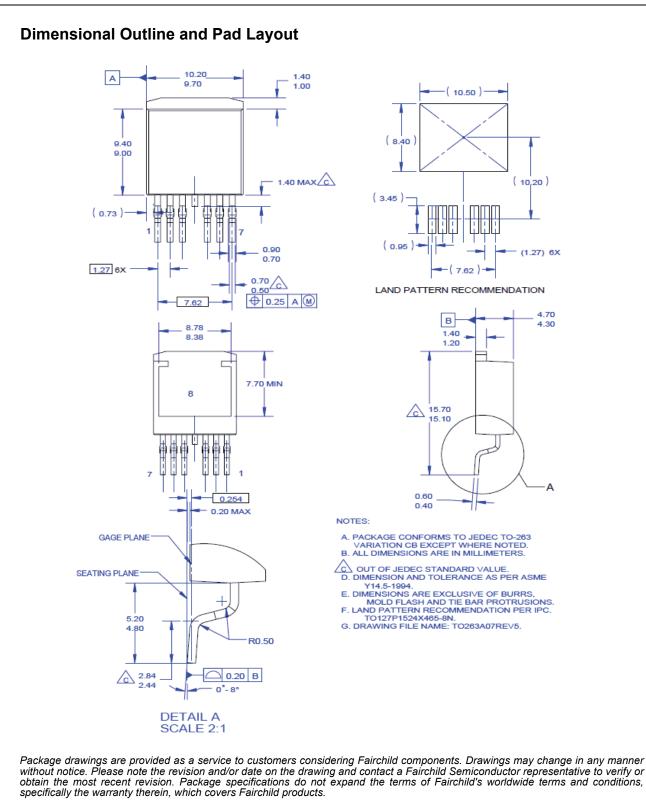
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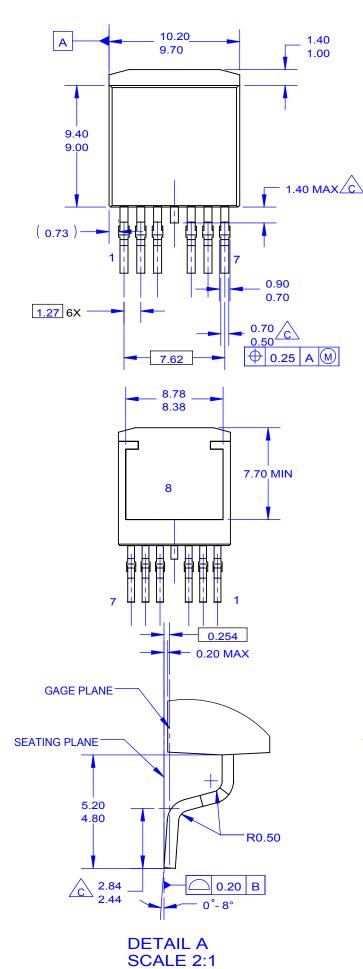
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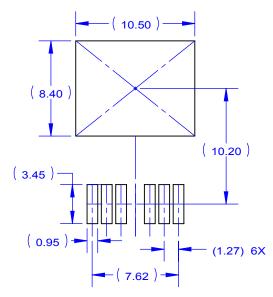
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Definition of Terms

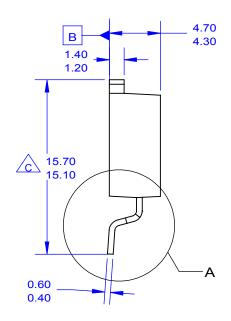
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|--|-----------------------|---|
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